

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING

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ABSTRACT

A method of processing a substrate according to the present disclosure includes: (a) supplying a first material containing a first element constituting a film to a substrate; (b) supplying a second material containing a second element constituting the film to the substrate; (c) supplying a third material containing a third element to be added to the film to the substrate; and (d) performing (a), (b), and (c) a predetermined number of times to form the film containing the first element, the second element, and the third element, wherein a difference between an electronegativity of the third element and an electronegativity of the second element is greater than a difference between an electronegativity of the first element and the electronegativity of the second element.

Fig. 4